

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Patent Application of )  
Hisashi OHTANI et al. )  
Based On Serial No. 08/633,307 ) Art Unit: 2811  
Which Was Filed: April 15, 1996 ) Examiner: W. Mintel  
For: A METHOD FOR MANUFACTURING )  
A SEMICONDUCTOR DEVICE ) Date: December 27, 2001



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4-24-02  
T. T. Loober

INFORMATION DISCLOSURE STATEMENT

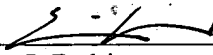
Commissioner for Patents  
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 08/633,307 filed April 15, 1996, and the predecessor applications including Serial Nos. 08/329,644; 08/430,623; 08/483,047 and 08/928,514.

Respectfully submitted,

  
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<b>Form PTO-1449</b> (Rev. 8-83)	U.S. Department of Commerce Patent and Trademark Office	Docket No: 740756-2415	Serial No. Not Yet Assigned
<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)			
		Applicant: Hisashi OHTANI et al.	
		Filing Date: December 27, 2001	Group: 2811

11002 U.S. PTO  
 10/026802  
 12/27/01

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Examiner	Date Considered
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\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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